Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- · Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Tin-plated 100 % solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV
- · AEC-Q101 qualified

## 3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	4	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 4 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	42	56	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



# **5. Pinning information**

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	15/	D
2	D	drain	7 7	
3	G	gate	2 5	G ←
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	8
7	D	drain		017aaa255
8	S	source		

# 6. Ordering information

## **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PMPB55ENEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

# 7. Marking

## **Table 4. Marking codes**

Type number	Marking code
PMPB55ENEA	2G

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
gate-source voltage			-20	20	V
drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	4	Α
	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	2.5	Α
peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	16	Α
non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = 1.3 A; DUT in avalanche (unclamped)		-	12.6	mJ
total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.65	W
	T <sub>sp</sub> = 25 °C		-	15.6	W
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
liode			'		'
source current	T <sub>amb</sub> = 25 °C	[1]	-	1.2	Α
rating					
electrostatic discharge voltage	НВМ	[2]	-	2000	V
	drain-source voltage gate-source voltage drain current  peak drain current non-repetitive drain-source avalanche energy total power dissipation  junction temperature ambient temperature storage temperature liode source current rating electrostatic discharge	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \\ \text{drain current} \\ \\ \end{array} \begin{array}{c} V_{GS} = 10 \text{ V}; \ T_{amb} = 25 \text{ °C} \\ \\ V_{GS} = 10 \text{ V}; \ T_{amb} = 100 \text{ °C} \\ \end{array} \begin{array}{c} \text{[1]} \\ \text{V}_{CS} = 10 \text{ V}; \ T_{amb} = 100 \text{ °C} \\ \end{array} \begin{array}{c} \text{[1]} \\ \text{peak drain current} \\ \text{non-repetitive drain-source avalanche} \\ \text{energy} \\ \end{array} \begin{array}{c} T_{j(init)} = 25 \text{ °C}; \ \text{single pulse}; \ t_p \leq 10 \text{ µs} \\ \\ T_{j(init)} = 25 \text{ °C}; \ \text{I}_D = 1.3 \text{ A}; \ \text{DUT in avalanche (unclamped)} \\ \text{energy} \\ \end{array} \begin{array}{c} \text{total power dissipation} \\ \\ T_{amb} = 25 \text{ °C} \\ \\ \hline \end{array} \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \\ \text{surce current} \\ \end{array} \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \end{array} \begin{array}{c} \text{[1]} \\ \\ \hline \end{array} \begin{array}{c} \text{Indicode} \\ \end{array} \\ \text{Source current} \\ \end{array} \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \end{array} \begin{array}{c} \text{[1]} \\ \hline \end{array} \begin{array}{c} \text{Indicode} \\ \end{array} \begin{array}{c} \text{[1]} \\ \end{array} \begin{array}{c} \text{Indicode} \\ \end{array} \end{array} \begin{array}{c} \text{[2]} \\ \end{array} $	$ \begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \end{array} \begin{array}{c} V_{GS} = 10 \text{ V}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{GS} = 10 \text{ V}; \ T_{amb} = 100 \text{ °C} \\ \end{array} \begin{array}{c} \text{[1]} \\ \text{-} \\ \hline V_{GS} = 10 \text{ V}; \ T_{amb} = 100 \text{ °C} \\ \end{array} \begin{array}{c} \text{[1]} \\ \text{-} \\ \hline V_{GS} = 10 \text{ V}; \ T_{amb} = 100 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \text{-} \\ \hline \end{array} \\ \text{non-repetitive drain-source avalanche energy} \\ \hline \text{total power dissipation} \\ \hline \text{total power dissipation} \\ \hline T_{amb} = 25 \text{ °C} \\ \hline T_{sp} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \hline T_{amb} = 25 \text{ °C} \\ \hline \end{array} \\ \hline \text{junction temperature} \\ \hline \text{ambient temperature} \\ \hline \text{storage temperature} \\ \hline \end{array} \begin{array}{c} -55 \\ \hline \text{storage temperature} \\ \hline \end{array} \\ \hline \text{source current} \\ \hline T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \hline \end{array} \\ \hline \text{-} \\ \hline \end{array} \\ \hline \text{electrostatic discharge} \\ \hline \end{array} \begin{array}{c} \text{HBM} \\ \hline \end{array} \begin{array}{c} \text{2} \\ \hline \end{array} \begin{array}{c} -20 \\ \hline \end{array} \\ \hline \end{array}$	

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [2] Measured between all pins.

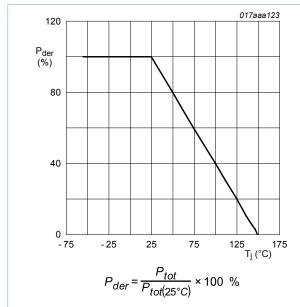


Fig. 1. Normalized total power dissipation as a function of junction temperature

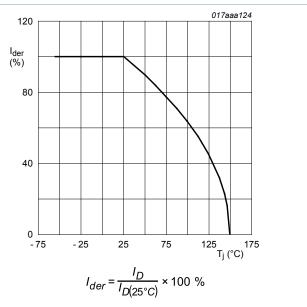


Fig. 2. Normalized continuous drain current as a function of junction temperature

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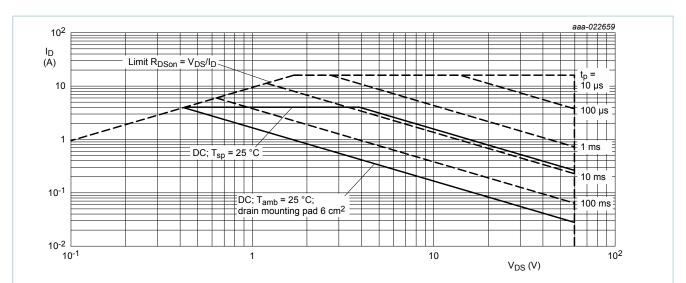


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	-	[1]	-	237	273	K/W
			[2]	-	66	76	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	4	8	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

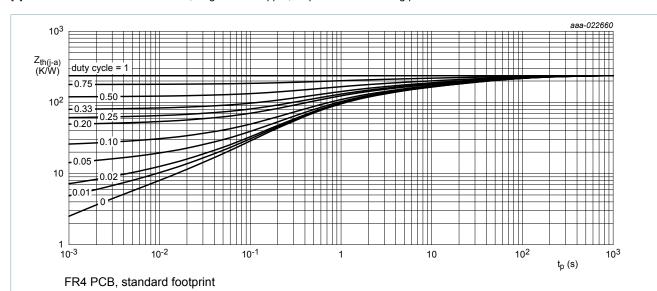


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

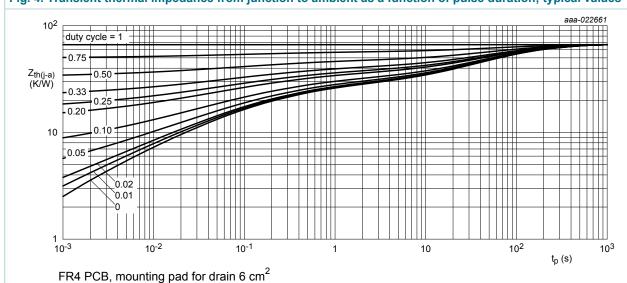


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	1.3	1.7	2.7	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
R <sub>DSon</sub> drain-sour resistance	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4 A; T <sub>j</sub> = 25 °C	-	42	56	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4 A; T <sub>j</sub> = 150 °C	-	80	106	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 3.5 A; $T_j$ = 25 °C	-	48	69	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 4 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	17	-	S
$R_G$	gate resistance	f = 1 MHz	-	2.7	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 4 \text{ A}; V_{GS} = 10 \text{ V};$	-	7.5	12	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	1.2	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	435	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	47	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	26	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; I_D = 4 \text{ A}; V_{GS} = 10 \text{ V};$	-	4.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	13.5	-	ns
t <sub>f</sub>	fall time		-	7	-	ns
Source-drai	in diode					,
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 1.2 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	_	0.8	1.2	V

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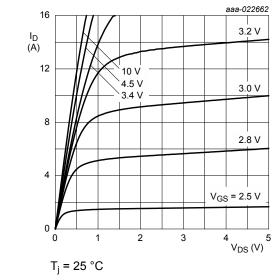


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

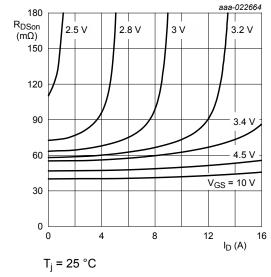


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

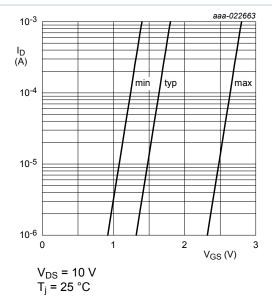


Fig. 7. Sub-threshold drain current as a function of gatesource voltage

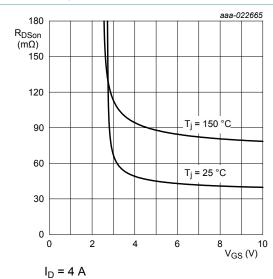


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

### 60 V, N-channel Trench MOSFET

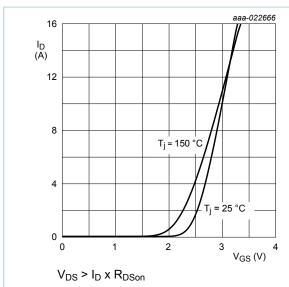


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

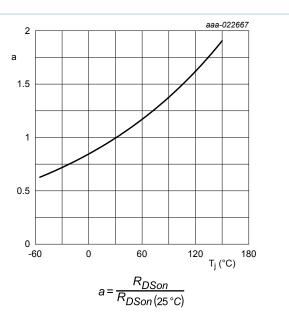


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

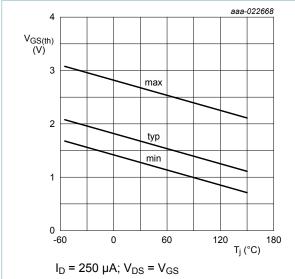


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

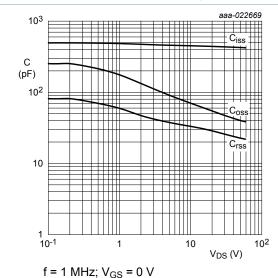


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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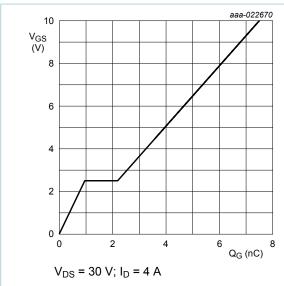


Fig. 14. Gate-source voltage as a function of gate charge; typical values

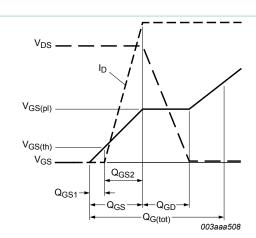


Fig. 15. Gate charge waveform definitions

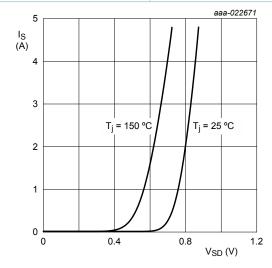
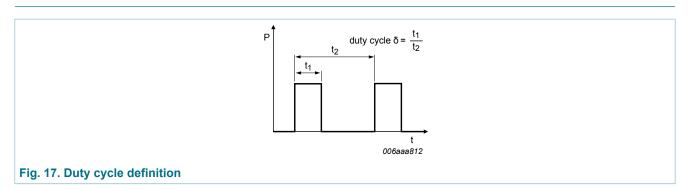


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 

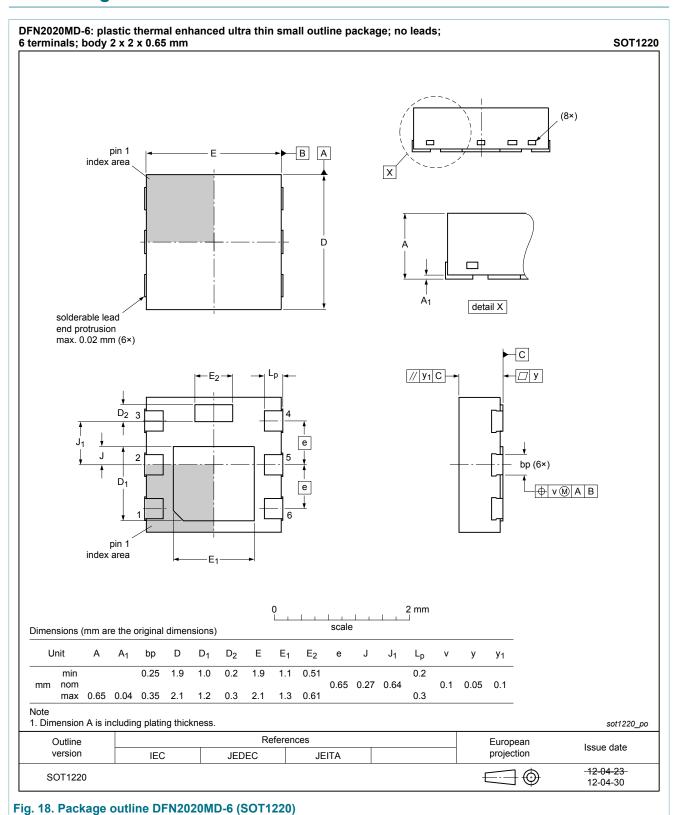


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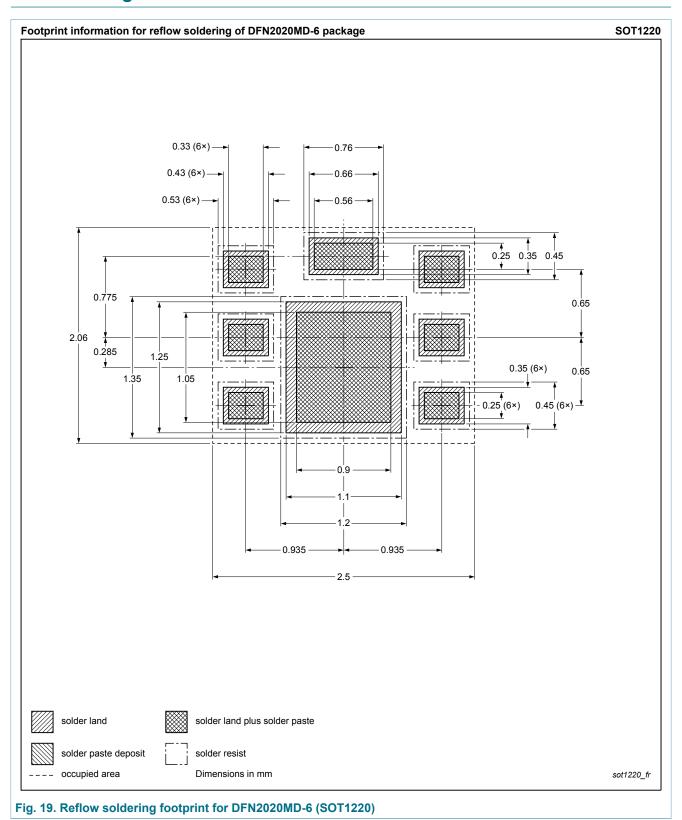
## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



# 13. Soldering



# 14. Revision history

## **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMPB55ENEA v.2	20160606	Product data sheet	-	PMPB55ENEA v.1				
Modifications:	Updated Figure 14							
PMPB55ENEA v.1	20160401	Preliminary data sheet	-	-				

#### 60 V, N-channel Trench MOSFET

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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**60 V, N-channel Trench MOSFET** 

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 06 June 2016

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